| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|---|---|---|---|---|---|---|
| L1 | 2 | "20050176170" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:40 |
| L2 | 2 | "20050212015" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:42 |
| L3 | 195914 | gate with electrodes | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:43 |
| L4 | 1619 | different with gate with electrode with material | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:43 |
| L5 | 166253 | gate adj electrode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:44 |
| L6 | 1579 | 4 and 5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:44 |
| L7 | 19 | different adj gate adj electrode adj material | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 18:11 |
| L8 | 10 | 7 and polysilicon | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 15:17 |
| L9 | 37 | "4399605" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 15:17 |
| L10 | 34 | 9 and polysilicon | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 15:18 |

| L11 | 34 | "6130123" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 15:56 |
|-----|----|-----------|----------|----|----|----------|
| L12 | 9  | 11 and SOI | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 15:56 |
| L13 | 4  | 7 and SOI | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 18:28 |
| L14 | 0  | 09/516073 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 18:20 |
| L15 | 2  | "6929992" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 18:28 |

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|---|---|---|---|---|---|---|
| L1 | 2 | "20050176170" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:40 |
| L2 | 2 | "20050212015" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:42 |
| L3 | 195914 | gate with electrodes | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:43 |
| L4 | 1619 | different with gate with electrode with material | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:43 |
| L5 | 166253 | gate adj electrode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:44 |
| L6 | 1579 | 4 and 5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 14:44 |
| L7 | 19 | different adj gate adj electrode adj material | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 18:11 |
| L8 | 10 | 7 and polysilicon | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 15:17 |
| L9 | 37 | "4399605" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 15:17 |
| L10 | 34 | 9 and polysilicon | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/15 15:18 |